2N3838

CASE 610A-04, STYLE 1

COMPLEMENTARY DUAL AMPLIFIER TRANSISTOR

NPN/PNP SILICON

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MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector 1 to Collector 2 Voltage Voltage Rating any Lead to Case	V_{C1C2}	±120 ±120		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
		One Die	**Both Die**	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.25 1.67	0.35 2.34	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	0.7 4.67	1.4 9.34	Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Emitter Nonmatching Voltage ($I_{C(on)}$ = 600 mAdc, $I_{B(on)}$ = 120 mAdc, $I_{B(off)}$ = 0)	$V_{CEO(NL)}$†	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current (V_{CE} = 50 Vdc, $V_{BE(off)}$ = 0.5 Vdc)	I_{BEV}	—	10	nAdc
Collector Cutoff Current (V_{CE} = 50 Vdc, $V_{BE(off)}$ = 0.5 Vdc) (V_{CE} = 50 Vdc, $V_{BE(off)}$ = 0.5 Vdc, T_A = 150°C)	I_{CEV}	— —	0.01 10	μAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc)(1) (I_C = 150 mAdc, V_{CE} = 10 Vdc)(1) (I_C = 150 mAdc, V_{CE} = 1.0 Vdc)(1)	h_{FE}	35 50 75 100 50	— — — 300 —	—
Collector-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{BE(sat)}$	0.85	1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	200	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz)	C_{obo}	—	8.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{ie}	1.6	9.0	kohms
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	60	300	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{oe}	—	50	μmho
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 kohm, f = 1.0 kHz)	NF	—	8.0	dB
SWITCHING CHARACTERISTICS				
Delay Time Rise Time	(V_{CC} = 10 Vdc, $V_{BE(off)}$ = 0 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d t_r	— —	10 40	ns ns
Storage Time Fall Time	(V_{CC} = 10 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s t_f	— —	250 90	ns ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

† The highest value of collector supply voltage that may be safely used with a resistive load switching circuit in which the collector current is 600 mAdc.